



# LEIGHTON ELECTRONICS INC.

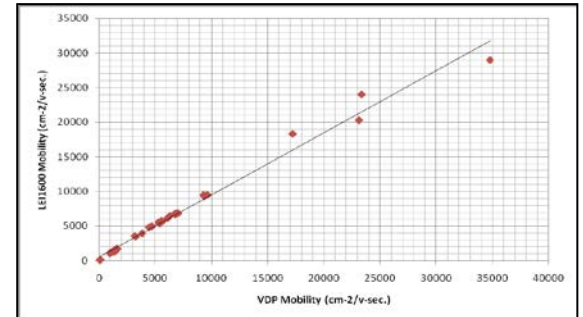
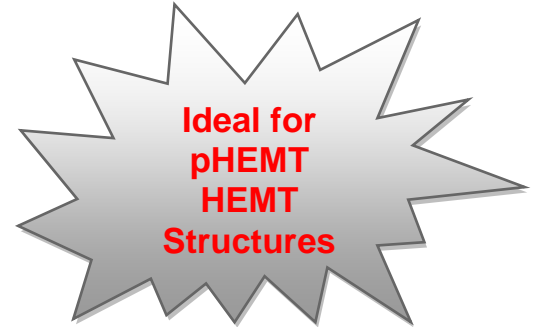
**LEIGHTON ELECTRONICS, INC.**  
Quality Service Since 1963  
P.O. Box 328  
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Lehigh, PA 18235-0328

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## Contactless Carrier Mobility/ Carrier Density/ Sheet Resistance Measurement and Mapping Systems

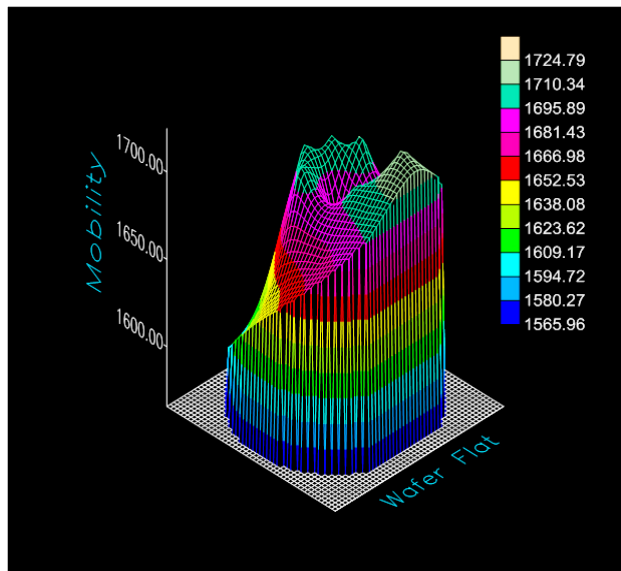


Figure 1: LEI1605AM - Measurement System

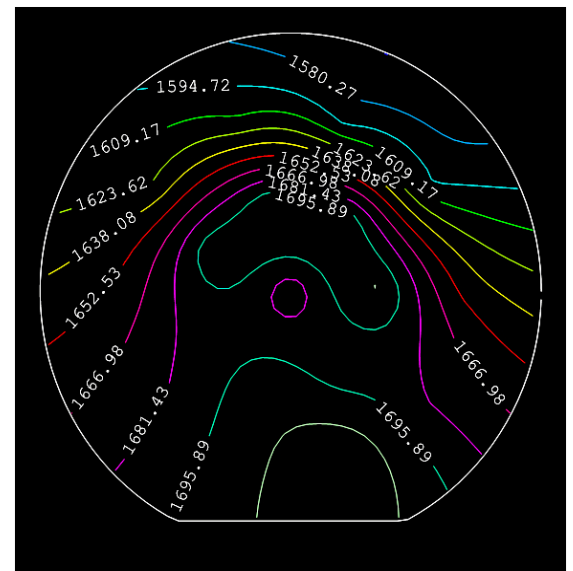


Correlation of mobility data obtained by van der Pauw Hall Measurements

LEI1605-AM



Surface Map



Contour Map

Nondestructive Measurement of Semiconductor Wafers





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LEI 1605-AM



SAB-0009 Rev 3.0

## Benefits vs. van der Pauw Hall

### Less Expensive

- \* No need to destroy samples
- \* Rapid ROI
- \* Minimal operator training required
- \* Carrier Concentration/Density

### Faster

- \* No sample preparation; shorter measurement time means immediate feedback on wafer transport properties

### Improved Repeatability

- \* Lead attachment = more consistent test conditions
- \* No variability

### Increase Utility

- \* No variability
- \* \*Automated system tuning
- \* Measure wafers at any point in the deposition or manufacturing process

### Wafer Mapping

- \* Up to 55 measurement points

### Characterization of

- \* GaAs, InP, InAs, GaN, AlN, Si, SiC based device structures: HEMTs, pHEMTs, HBTs, FETs, (epi on semi insulating and some doped substrates)

## Performance and Features

### Measurement Features

- \* Hall Mobility
- \* Hall Coefficient
- \* Sheet Resistance
- \* Carrier Concentration/Density

### Measurement Capabilities

- \* Sample thickness range of 450 to 1000 microns
- \* Normal wafer gap (>/= .060 mils)
- \* Manual loading
- \* Size: 2" to 8" wafers

### Measurement Resolution Options

- \* 21 mm or 14 mm diameter
- \* Measurement gap adjustment

### Magnet

- \* Permanent 2.5 - 3.0Kgauss (0.25 - 0.30T)

Specifications	
Measure	Measurement ranges
Mobility	~ 600 - 20,000 cm <sup>2</sup> /.sec
Sheet Res.	~ 100 - 3,000 ohm/ sq.

### \* Dynamic Repeatability

1% to 4% depends on the range

### \* Static Repeatability < ± 1%

1% to 2% depends on the range

### \* Accuracy (estimated) < ± 10%

\* Specifications subject to change; contact LEI for the latest.

Nondestructive Measurement of Semiconductor Wafers